# RENESAS

## HD74AC165 Parallel-Load 8-bit Shift Register

REJ03D0254–0200Z (Previous ADE-205-374 (Z)) Rev.2.00 Jul.16.2004

#### Description

This 8-bit serial shift register shifts data from  $Q_A$  to  $Q_H$  when clocked, Parallel inputs to each stage are enabled by a low level at the Shift/Load Input. Also included is a gated clock input and a complementary output from the eighth bit.

Clocking is accomplished through a 2-input NOR gate permitting one input to be used as a clock inhibit function. Holding either of the clock inputs high inhibits clocking, and holding either clock input low with the Shift/Load input high enables the other clock input. Data transfer occurs on the positive going edge of the clock. Parallel loading is inhibited as long as the Shift/Load input is high. When taken low, data at the parallel inputs is loaded directly into the register independent of the state of the clock.

#### Features

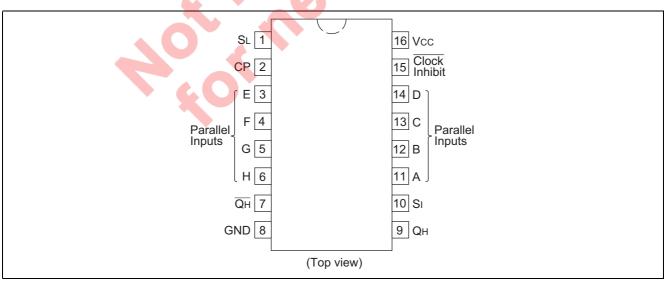
- Outputs Source/Sink 24 mA
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74AC165FPEL	SOP-16 pin (JEITA)	FP-16DAV	FP	EL (2,000 pcs/reel)
HD74AC165RPEL	SOP-16 pin (JEDEC)	FP-16DNV	RP	EL (2,500 pcs/reel)

Notes: 1. Please consult the sales office for the above package availability.

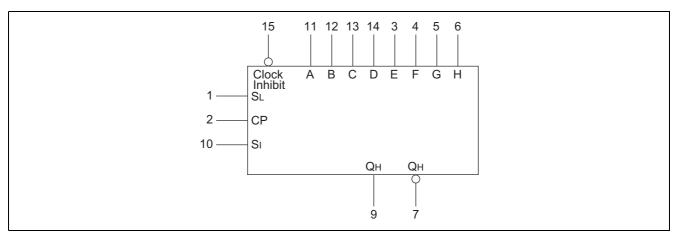
2. The packages with lead-free pins are distinguished from the conventional products by adding V at the end of the package code.

#### **Pin Arrangement**





#### Logic Symbol



#### **Pin Names**

A to H	Parallel Inputs
SI	Serial Input
CP	Clock Input
$S_L$	Shift Load
Clock Inhibit	Clock Inhibit
$Q_{\rm H}, \overline{Q}_{\rm H}$	Outputs

### **Truth Table**

$S_{I}$	Seria	l Input								
СР	Clock	k Input								
$S_L$	Shift	Load								
Clock II	nhibit Clocl	k Inhibit								
$Q_{\rm H}, \overline{Q}_{\rm H}$	Outp	uts								
Truth Ta	able									
		Inputs								
	Clock			Parallel	Internal Outputs Output					
S∟	Inhibit	СР	S	AH	Q <sub>A</sub>	Q <sub>B</sub>	Q <sub>H</sub>			
L	Х	Х	X	ah	а	b	h			
Н	L	L	X	X	$Q_{A\overline{D}}$	$Q_{B\overline{O}}$	Q <sub>HO</sub>			
Н	L		H	X	н	Q <sub>An</sub>	Q <sub>Gn</sub>			
Н	L		L	X	L	Q <sub>An</sub>	Q <sub>Cn</sub>			
н	Н	X	Х	X	$Q_{A\overline{D}}$	$Q_{B\overline{O}}$	Q <sub>HO</sub>			

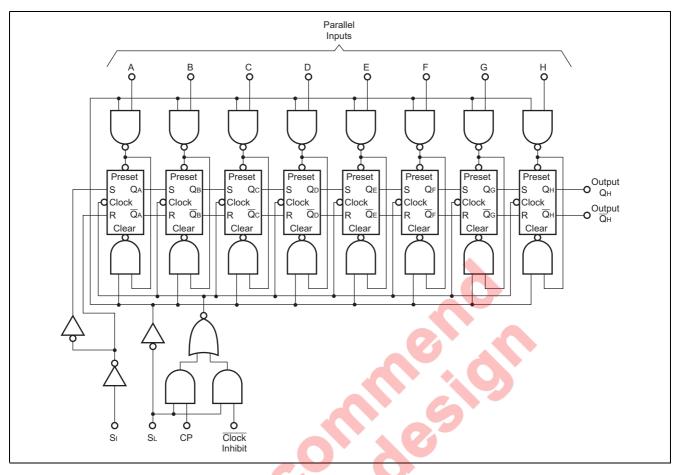
High Voltage Level Н: Low Voltage Level

L : X : Immaterial

\_\_\_: Low-to-High Clock Transition



### Logic Diagram



### Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Condition
Supply voltage	V <sub>cc</sub>	–0.5 to 7	V	
DC input diode current	I <sub>IK</sub>	-20	mA	$V_1 = -0.5V$
		20	mA	$V_1 = Vcc+0.5V$
DC input voltage	V	-0.5 to Vcc+0.5	V	
DC output diode current	I <sub>ок</sub>	-50	mA	$V_0 = -0.5V$
		50	mA	$V_{O} = Vcc+0.5V$
DC output voltage	Vo	-0.5 to Vcc+0.5	V	
DC output source or sink current	I <sub>o</sub>	±50	mA	
DC $V_{cc}$ or ground current per output pin	I <sub>CC</sub> , I <sub>GND</sub>	±50	mA	
Storage temperature	Tstg	-65 to +150	°C	

### **Recommended Operating Conditions**

Item	Symbol	Ratings	Unit	Condition
Supply voltage	V <sub>cc</sub>	2 to 6	V	
Input and output voltage	V <sub>I</sub> , V <sub>O</sub>	0 to V <sub>cc</sub>	V	
Operating temperature	Та	-40 to +85	°C	
Input rise and fall time	tr, tf	8	ns/V	$V_{CC} = 3.0V$
(except Schmitt inputs)				$V_{\rm CC} = 4.5 \ V$
$V_{IN}$ 30% to 70% $V_{CC}$				V <sub>cc</sub> = 5.5 V



#### **DC Characteristics**

ltem	Sym- bol	Vcc (V)	1	Га = 25°(	C	Ta = -40 to +85°C		Unit	Condition
			min.	typ.	max.	min.	max.		
Input Voltage	V <sub>IH</sub>	3.0	2.1	1.5	—	2.1	—	V	$V_{OUT} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$
		4.5	3.15	2.25	—	3.15	—		
		5.5	3.85	2.75	—	3.85	—		
	V <sub>IL</sub>	3.0	—	1.50	0.9	—	0.9		$V_{OUT} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$
		4.5	—	2.25	1.35	—	1.35		
		5.5	—	2.75	1.65	—	1.65		
Output voltage	V <sub>OH</sub>	3.0	2.9	2.99	_	2.9	—	V	$V_{IN} = V_{IL} \text{ or } V_{IH}$
		4.5	4.4	4.49	_	4.4	—		$I_{OUT} = -50 \ \mu A$
		5.5	5.4	5.49	_	5.4	—		
		3.0	2.58	_	_	2.48	—		$V_{IN} = V_{IL} \text{ or } V_{IH}$ $I_{OH} = -12 \text{ mA}$
		4.5	3.94	_	_	3.80	—		I <sub>OH</sub> = -24 mA
		5.5	4.94	_	_	4.80	—		I <sub>он</sub> = -24 mА
	V <sub>OL</sub>	3.0	—	0.002	0.1	—	0.1		$V_{IN} = V_{IL} \text{ or } V_{IH}$
		4.5	—	0.001	0.1	—	0.1		I <sub>ουτ</sub> = 50 μA
		5.5	—	0.001	0.1	—	0.1		
		3.0	—	_	0.32	—	0.37		$V_{IN} = V_{IL} \text{ or } V_{IH}$ $I_{OL} = 12 \text{ mA}$
		4.5	—	_	0.32	-	0.37		I <sub>oL</sub> = 24 mA
		5.5	—	—	0.32		0.37		I <sub>OL</sub> = 24 mA
Input leakage current	I <sub>IN</sub>	5.5	—	—	±0.1		±1.0	μA	$V_{IN} = V_{CC}$ or GND
Dynamic output	I <sub>OLD</sub>	5.5	<b> </b>	—		86		mA	V <sub>OLD</sub> = 1.1 V
current*	I <sub>OHD</sub>	5.5	1—	—		-75		mA	V <sub>OHD</sub> = 3.85 V
Quiescent supply current	I <sub>cc</sub>	5.5	—	5	8.0	-0	80	μA	$V_{IN} = V_{CC}$ or ground

\*Maximum test duration 2.0 ms, one output loaded at a time.

### **AC Characteristics**

			Ta = +25°C C <sub>1</sub> = 50 pF				C to +85°C 50 pF	
Item	Symbol	V <sub>cc</sub> (V)* <sup>1</sup>	Min	<u>с_ оор</u> Тур	Max	Min	Max	Unit
Maximum count	f <sub>max</sub>	3.3	85	—	_	70		MHz
frequency		5.0	100	—	—	90	—	
Propagation delay	t <sub>PLH</sub>	3.3	1.0	11.0	17.5	1.0	20.5	ns
CP to $Q_H$ or $\overline{Q}_H$		5.0	1.0	8.0	11.5	1.0	13.5	
Propagation delay	t <sub>PHL</sub>	3.3	1.0	12.0	18.0	1.0	21.5	ns
CP to $Q_H$ or $\overline{Q}_H$		5.0	1.0	8.5	12.5	1.0	14.5	
Propagation delay	t <sub>PLH</sub>	3.3	1.0	13.5	19.5	1.0	22.5	ns
H to $Q_H$ or $\overline{Q}_H$		5.0	1.0	9.5	13.5	1.0	15.5	
Propagation delay	t <sub>PHL</sub>	3.3	1.0	9.0	14.0	1.0	16.5	ns
H to $Q_H$ or $\overline{Q}_H$		5.0	1.0	6.5	9.5	1.0	11.0	
Propagation delay	t <sub>PLH</sub>	3.3	1.0	11.5	20.5	1.0	23.5	ns
$S_L$ to $Q_H$ or $\overline{Q}_H$		5.0	1.0	8.5	14.0	1.0	16.0	
Propagation delay	t <sub>PHL</sub>	3.3	1.0	10.0	16.5	1.0	19.5	ns
$S_L$ to $Q_H$ or $\overline{Q}_H$		5.0	1.0	7.5	11.0	1.0	12.5	

Note: 1. Voltage Range 3.3 is  $3.3 \text{ V} \pm 0.3 \text{ V}$ 

Voltage Range 5.0 is 5.0 V  $\pm$  0.5 V



### AC Operating Requirements

			Ta = +25°C C <sub>L</sub> = 50 pF		Ta = -40°C to +85°C C <sub>L</sub> = 50 pF	
ltem	Symbol	V <sub>cc</sub> (V)* <sup>1</sup>	Тур	Guarantee	d Minimum	Unit
Setup time, HIGH or LOW	t <sub>su</sub>	3.3	3.5	5.0	6.0	ns
H to $S_L$		5.0	2.5	4.0	4.5	
Hold time, HIGH or LOW	t <sub>h</sub>	3.3	-1.0	0.5	0.5	ns
H to $S_L$		5.0	-0.5	0.5	0.5	
Setup time, HIGH or LOW	t <sub>su</sub>	3.3	1.0	3.5	4.0	ns
S <sub>in</sub> to CP		5.0	0.5	3.0	3.5	
Hold time, HIGH or LOW	t <sub>h</sub>	3.3	1.5	2.0	2.0	ns
S <sub>in</sub> to CP		5.0	1.0	2.0	2.0	
Setup time, HIGH or LOW	t <sub>su</sub>	3.3	3.0	5.0	6.0	ns
S <sub>L</sub> to CP		5.0	2.0	4.0	4.5	
Hold time, HIGH or LOW	t <sub>h</sub>	3.3	-2.0	0.0	0.0	ns
S <sub>L</sub> to CP		5.0	-1.0	0.0	0.0	
Recovery time clock inhibit	t <sub>rec</sub>	3.3	2.5	3.5	3.5	ns
to CP		5.0	2.0	3.0	3.0	
Clock pulse width	t <sub>w</sub>	3.3	3.0	5.5	7.0	ns
		5.0	3.0	4.5	5.0	

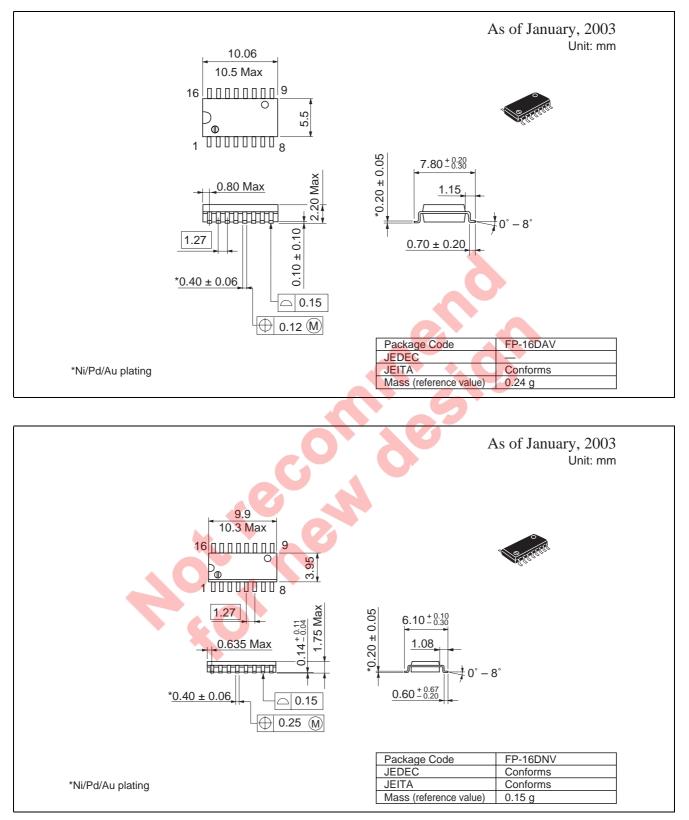
Note: 1. Voltage Range 3.3 is  $3.3 \text{ V} \pm 0.3 \text{ V}$ Voltage Range 5.0 is  $5.0 \text{ V} \pm 0.5 \text{ V}$ 

### Capacitance

ltem	Symbol	Тур	Unit	Condition
Input capacitance	C <sub>IN</sub>	4.5	pF	$V_{\rm CC} = 5.5 \text{ V}$
Power dissipation capacitance	C <sub>PD</sub>	50	pF	$V_{\rm CC} = 5.0 \text{ V}$



#### **Package Dimensions**





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